

## **AMENDMENTS TO THE CLAIMS**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

### **Listing of Claims:**

**Claim 1 (currently amended):** A semiconductor device module structure comprising:

- a high-resistance layer of a first conductive type;
- a base layer of a second conductive type formed in an upper part of the high-resistance layer of the first conductive type;
- an emitter region of a first conductive type formed in an upper part of the base layer of the second conductive type;
- an emitter electrode connected to the emitter region;
- an insulated gate electrode adjacent to the base layer of the second conductive type;
- a guard ring part ~~where diffusion~~, wherein a portion of the guard ring has been made deep around a cell region including the emitter region ~~has been made deep~~;
- a passivation layer formed on ~~the~~ an upper part of the guard ring part and not extending onto ~~the~~ an upper part of the cell region;
- a buffer layer of a first conductive type formed on an underside of the high-resistance layer of the first conductive type;

a collector layer of the second conductive type formed on ~~the~~an  
underside of ~~a~~the buffer layer of the first conductive type;  
a collector electrode connected to the collector layer; and  
a metal flat plate upper heat-sinking part connected to the emitter  
electrode at a height such that it is non-contacting with the passivation film.

**Claim 2 (currently amended):** The semiconductor device module structure  
of claim 1, ~~characterized in that the module structure of a~~wherein the semiconductor  
device module structure further comprises a diode part, and wherein a cathode  
electrode atlocated in an upper part of the diode part between the high-resistance  
layer and the upper heat-sinking part areis connected to the upper heat-sinking part.

**Claim 3 (new):** The semiconductor device module structure of claim 1,  
wherein one end of the metal flat plate upper heat-sinking part is connected to the  
emitter electrode and the opposite end of the metal flat plate heat-sinking part is  
connected to a substrate.